V_{CES}	Collector-emitter voltage	1200

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CES	Collector-emitter breakdown voltage	GE=0V, I_C=250μA	1200	-	-	V
CES	Collector-emitter leakage current	CE=1200V, GE=0V	-	-	100	μA
GES	Gate leakage current, forward	GE=20V, CE=0V	-	-	100	nA
	Gate leakage current, reverse	GE=-20V, CE=0V	-	-	-100	nA
GE(th)	Gate-emitter threshold voltage	GE= CE, C=1mA	5.2	5.6	6.0	V
CE(sat)	Collector-emitter saturation voltage	GE=15 V, C=75A	-	2.0	-	V
		GE=15V, C=75A, vj=175	-	2.6	-	V

($_{vj}$=25 unless otherwise specified)

$_{F}$	Diode forward voltage	$_{F}$=75A	-	2.1	-	V
		$_{F}$=75A $_{vj}$=175	-	1.8	-	V
$_{rr}$	Diode reverse recovery time	$_{R}$=600V $_{F}$=75A d $_{F}$/d =-600A/μs	-	163	-	ns
$_{rrm}$	Diode peak reverse recovery current		-	20	-	A
$_{rr}$	Diode reverse recovery charge		-	2046	-	nC
$_{rr}$	Diode reverse recovery time	$_{R}$=600V $_{F}$=75A d $_{F}$/d =-600A/μs $_{vj}$=175	-	278	-	ns
$_{rrm}$	Diode peak reverse recovery current		-	39	-	A
$_{rr}$	Diode reverse recovery charge		-	6679	-	nC

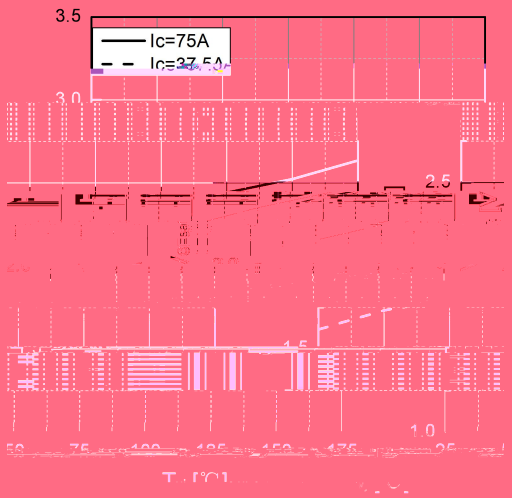


Fig 7. Typical $_{CEsat}$ as a function of $_{vj}$

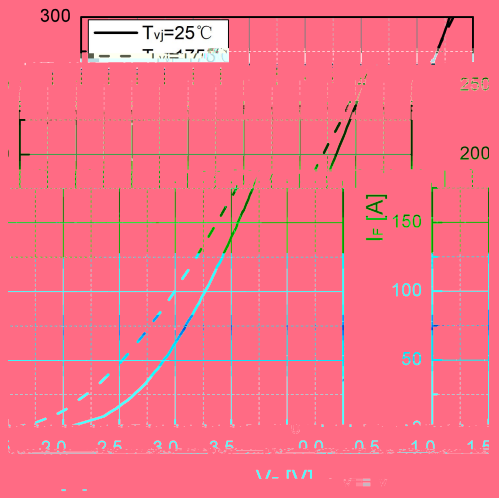


Fig 8. Typical $_{F}$ as a function of $_{F}$

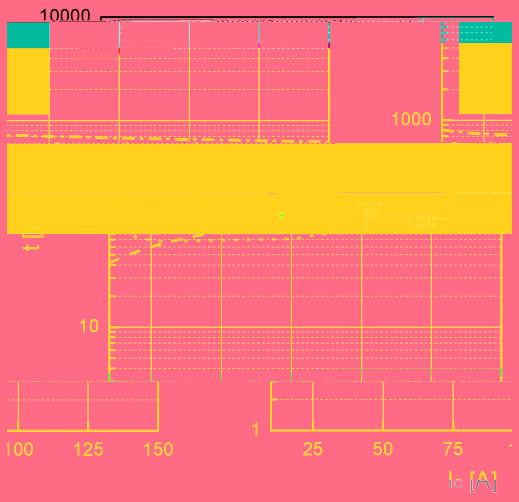


Fig 9. Typical switching time as a function of $_{C}$

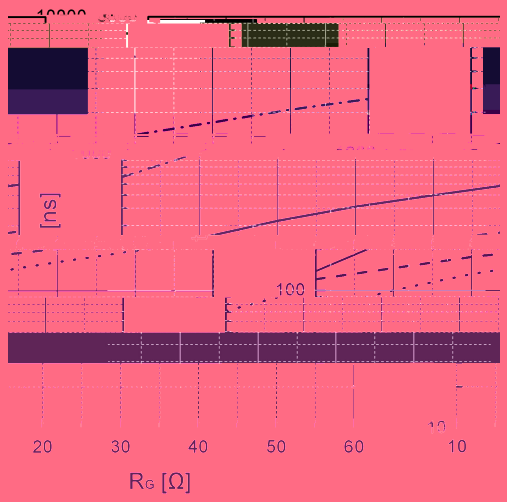


Fig 10. Typical switching times as a function of $_{G}$

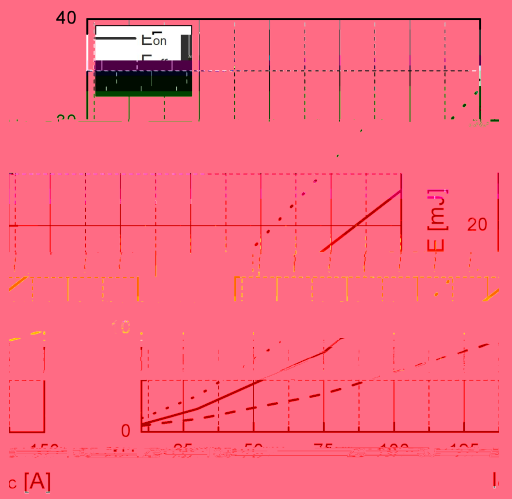


Fig 11. Typical switching energy losses as a function of $_{C}$

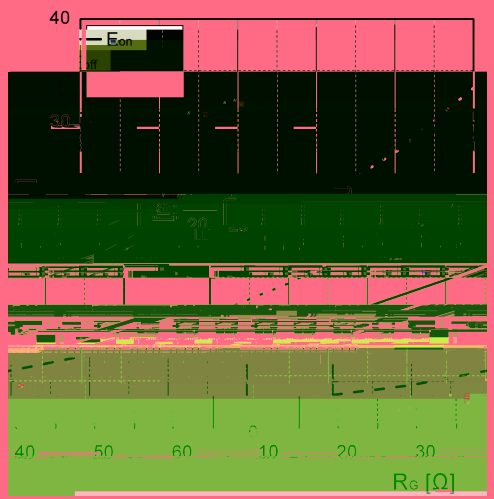
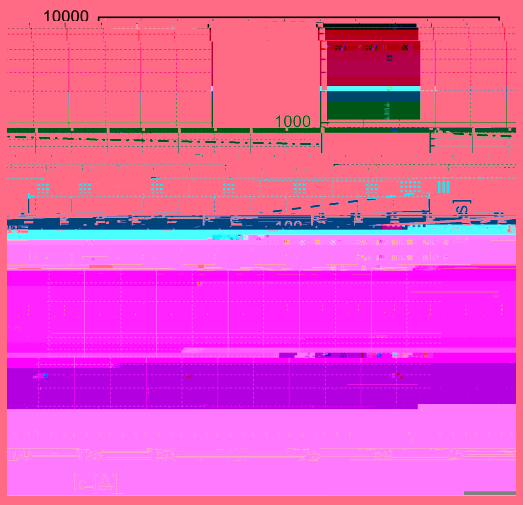
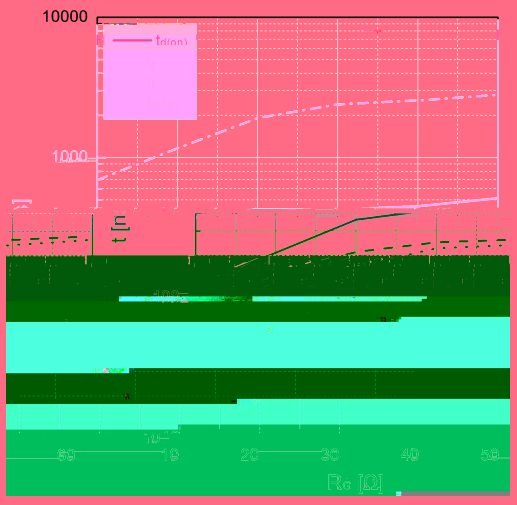


Fig 12. Typical switching energy losses as a function of $_{G}$

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Date	Revision	Changes
2025-01-26	Rev. 1.2	Add SOA and Rth graph
2025-02-17	Rev. 1.3	Modify the package size
2025-03-03	Rev. 2.0	Replace sketch
2026-06-26	Rev. 2.1	Update thermal

PLEASE NOTE - Jiangsu JieJie Microelectronics Co., Ltd ("JJM") reserves the right to amend, correct, modify

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